



isc N-Channel MOSFET Transistor

FEATURES

- Drain Current : I_D= 12A@ T_C=25℃
- Drain Source Voltage
 - : V_{DSS}= 250V(Min)
- Static Drain-Source On-Resistance
 - : $R_{DS(on)} = 0.3 \Omega (Max) @ V_{GS} = 10V$
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



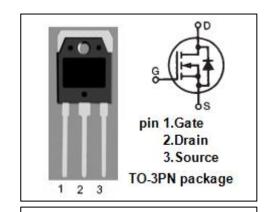
 motor drive, DC-DC converter, power switch and solenoid drive.

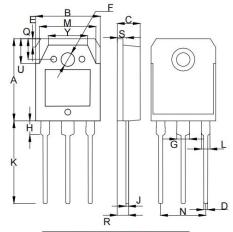
ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

| SYMBOL | PARAMETER | VALUE | UNIT | |
|------------------|--|---------|------------|--|
| V _{DSS} | Drain-Source Voltage | 250 | V | |
| V _{GS} | Gate-Source Voltage-Continuous | ±20 | V | |
| I _D | Drain Current-Continuous | 12 | А | |
| I _{DM} | Drain Current-Single Pluse | 48 | А | |
| P _D | Total Dissipation @T _C =25℃ | 100 | W | |
| TJ | Max. Operating Junction Temperature | -55~150 | $^{\circ}$ | |
| T _{stg} | Storage Temperature | -55~150 | $^{\circ}$ | |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | MAX | UNIT |
|---------------------|--------------------------------------|------|------|
| R _{th j-c} | Thermal Resistance, Junction to Case | 1.25 | °C/W |





| DIM | n | nm |
|-------|-------|-------|
| Dilvi | MIN | MAX |
| Α | 19.60 | 20.30 |
| В | 15.30 | 15.90 |
| С | 4.70 | 4.90 |
| D | 0.90 | 1.10 |
| E | 1.90 | 2.10 |
| F | 3.40 | 3.60 |
| G | 2.90 | 3.20 |
| Н | 3.20 | 3.40 |
| J | 0.595 | 0.605 |
| K | 19.80 | 20.70 |
| L | 1.90 | 2.20 |
| M | 13.30 | 13.90 |
| N | 10.89 | 10.91 |
| Q | 4.25 | 5.10 |
| R | 3.30 | 3.45 |
| S | 1.995 | 2.100 |
| U | 5.90 | 6.20 |
| Υ | 9.90 | 10.10 |

isc website: www.iscsemi.com

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2SK948

ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | MAX | UNIT |
|----------------------|---------------------------------|---|-----|------|------|
| V _{(BR)DSS} | Drain-Source Breakdown Voltage | V _{GS} = 0; I _D = 1.0mA | 250 | | V |
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} = 10V; I _D = 1.0mA | 2.1 | 4.0 | V |
| R _{DS(on)} | Drain-Source On-Resistance | V _{GS} = 10V; I _D = 6.0A | | 0.3 | Ω |
| I _{GSS} | Gate-Body Leakage Current | V _{GS} = ±20V;V _{DS} = 0 | | ±0.1 | uA |
| I _{DSS} | Zero Gate Voltage Drain Current | V _{DS} = 250V; V _{GS} = 0 | | 500 | uA |
| V _{SD} | Forward On-Voltage | I _S = 12A; V _{GS} = 0 | | 1.5 | V |



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